

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions of claims in the application.

1-2. (Canceled)

3. (Currently Amended) ~~The manufacturing method of the semiconductor device according to claim 2~~ A manufacturing method of a semiconductor device which is formed with a bipolar transistor being composed by including a base, an emitter and a collector on a semiconductor substrate, comprising the steps of:

forming a multilayer film on said semiconductor substrate, and forming an opening, which is opened on said base and said emitter, in the multilayer film;

forming on an entire surface a compound semiconductor film which contains silicon and an other semiconductor element, and has a composition with a high content of silicon in an upper layer region and a lower layer region, and a high content of the other semiconductor element in an intermediate layer region;

performing anisotropic dry etching for the compound semiconductor film so as to reach a certain height of the opening, but performing no isotropic etching,

wherein the anisotropic dry etching is performed for the compound semiconductor film in a high vacuum state; and

further comprising the step of:

performing quasi-anisotropic dry etching for the compound semiconductor film in a low vacuum state after the anisotropic dry etching is performed for the compound semiconductor film in the high vacuum state.

4. (Canceled)

5. (Original) The manufacturing method of the semiconductor device according to claim 3, wherein atmospheric pressure in the low vacuum state is 133 (Pa) or higher.

6. (Canceled)

7. (Original) The manufacturing method of the semiconductor device according to claim 3, wherein atmospheric pressure in the low vacuum state is about 40×10^2 (Pa).

8-9. (Canceled)

10. (Currently Amended) ~~The manufacturing method of the semiconductor device according to claim 9~~ A manufacturing method of a semiconductor device, comprising the steps of:

forming a thin film on a semiconductor substrate, and forming an opening in part of the thin film;

forming on an entire surface a compound semiconductor film which contains a first semiconductor element and a second semiconductor element, and has a composition with a high content of the first semiconductor element in an upper layer region and a lower layer region, and a high content of the second semiconductor element in an intermediate layer region;

performing anisotropic dry etching for the compound semiconductor film so as to reach a certain height of the opening, but performing no isotropic etching,

wherein the anisotropic dry etching is performed for the compound semiconductor film in a high vacuum state; and

further comprising the step of: performing quasi-anisotropic dry etching for the compound semiconductor film in a low vacuum state after the anisotropic dry etching is performed for the compound semiconductor film in the high vacuum state.

11-12. (Canceled)

13. (Original) The manufacturing method of the semiconductor device according to claim 10, wherein atmospheric pressure in the low vacuum state is 133 (Pa) or higher.

14. (Canceled)

15. (Original) The manufacturing method of the semiconductor device according to claim 10, wherein atmospheric pressure in the low vacuum state is about 40×10^2 (Pa).

16-17. (Canceled)

18. (Original) The manufacturing method of the semiconductor device according to claim 3, wherein the compound semiconductor film comprises an SiGe film or an SiGeC film.

19-20. (Canceled)

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21. (Original) The manufacturing method of the semiconductor device according to claim 10, wherein the compound semiconductor film comprises an SiGe film or an SiGeC film.

22. (Canceled)